

NUMERICAL SIMULATION  
OF THE PHOTOCURRENT IN THE THIN METAL —  
SILICON STRUCTURES WITH QUANTUM WELLS

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S u m m a r y

Using the SimWindows program package, we have numerically calculated the photocurrents in the space-charge region of thin metal—silicon structures with quantum wells (QWs) as well as their dependences on the geometrical size and the number of the QWs, and on the doping level. A possibility of creating the photosensitive structures on the basis of the layers of porous silicon with various degree of porosity has been analyzed.